

1N4148WGH

Silicon Epitaxial Planar Switching Diode

Lead free product

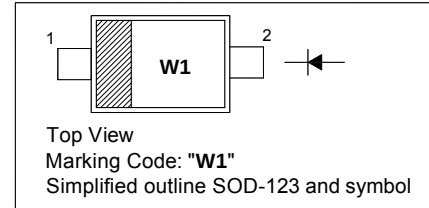
Halogen-free type

Features

- SOD-123 package
- Fast switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



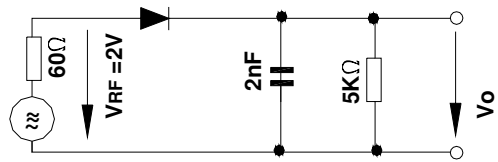
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Maximum DC Blocking Voltage	V_{DC}	75	V
Average Rectified Current Half Wave Rectification with Resistive Load $f \geq 50$ Hz	$I_{F(AV)}$	150	mA
Non-repetitive Peak Forward Surge Current at $t = 1 \mu\text{s}$	I_{FSM}	4	A
Power Dissipation	P_{tot}	410	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	312	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

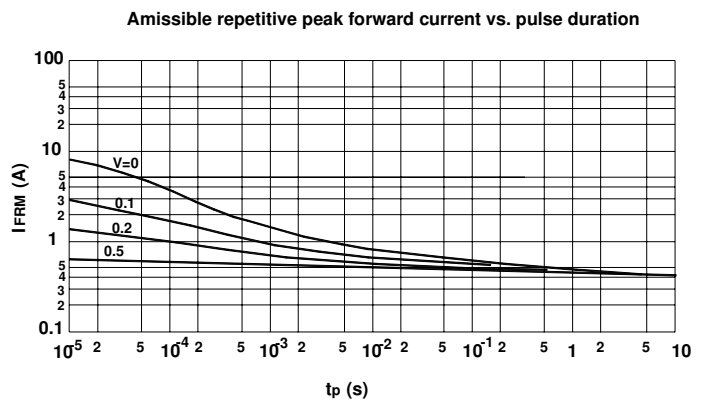
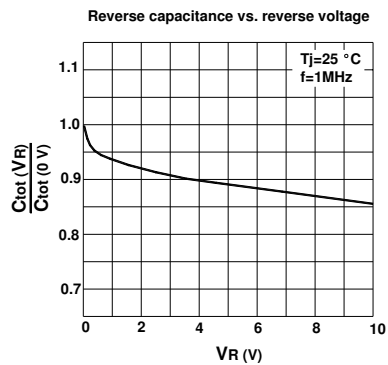
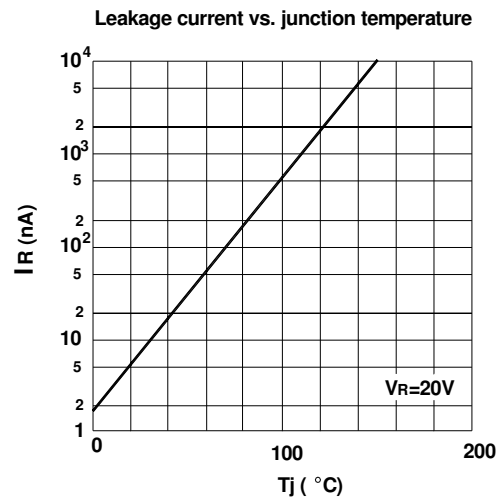
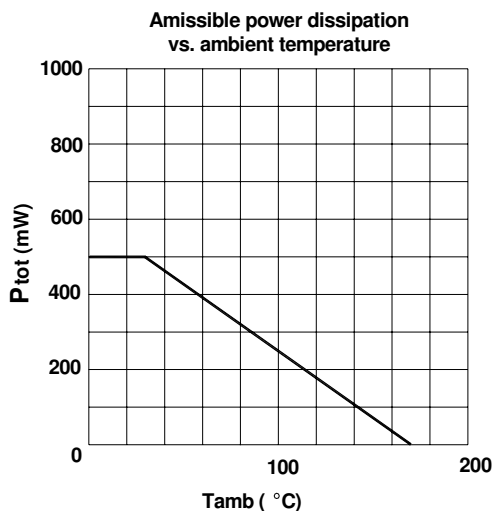
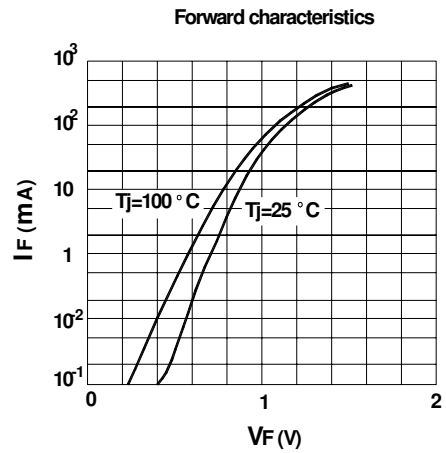
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 50$ mA at $I_F = 150$ mA	V_F	- - - -	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 20$ V at $V_R = 75$ V at $V_R = 20$ V, $T_J = 150^\circ\text{C}$	I_R	- - -	25 5 50	nA μA μA
Capacitance at $V_F = V_R = 0$ V	C_{tot}	-	4	pF
Reverse Recovery Time from $I_F = 10$ mA to $I_R = 1$ mA, $V_R = 6$ V, $R_L = 100 \Omega$	t_{rr}	-	4	ns

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Rectification Efficiency Measurement Circuit

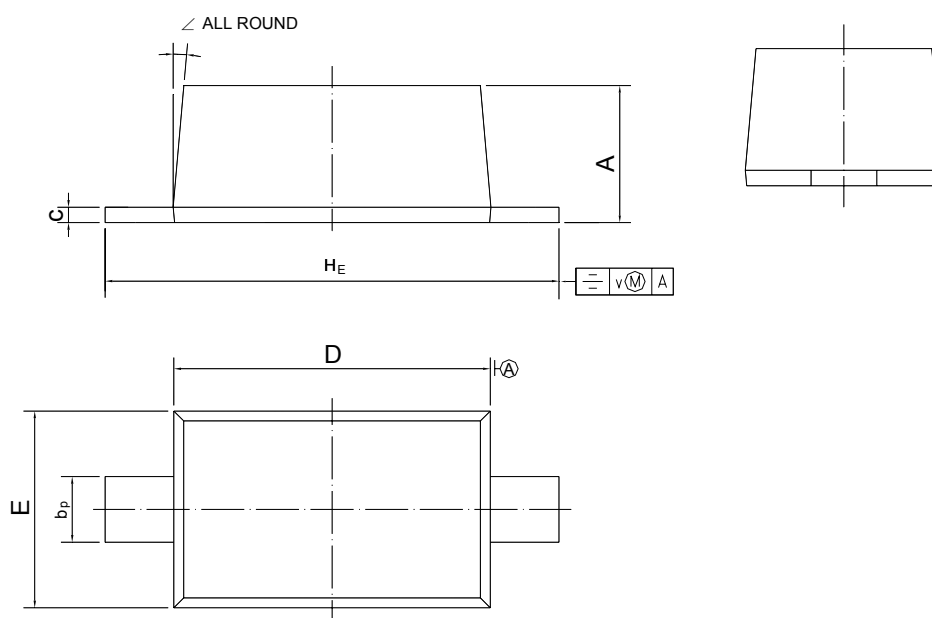


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°